

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	1079206	(detector or photodetector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:36
L5	2106205	(detector or photodetector or photodetecting or detecting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:36
L6	9195	(detector or photodetector or photodetecting or detecting) and (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:37
L7	5873	(detector or photodetector or photodetecting or detecting) and (semiconductor adj layer) and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:37
L8	703	(detector or photodetector or photodetecting or detecting) and (semiconductor adj layer) and electrode and GaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:37
L9	121	(detector or photodetector or photodetecting or detecting) and (semiconductor adj layer) and electrode and GaN.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:37
L10	45	(detector or photodetector or photodetecting or detecting) and (semiconductor adj layer) and electrode.clm. and GaN.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:37
L11	20	(detector or photodetector or photodetecting or detecting) and (semiconductor adj layer).clm. and electrode.clm. and GaN.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:37
L12	5	(detector or photodetector or photodetecting or detecting).clm. and (semiconductor adj layer).clm. and electrode.clm. and GaN.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:40

L13	187	(detector or photodetector or photodetecting or detecting).clm. with (semiconductor adj layer). clm. and electrode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:40
L14	112	(detector or photodetector or photodetecting or detecting).clm. with (semiconductor adj layer). clm. with electrode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:40
L15	0	(detector or photodetector or photodetecting or detecting).clm. with (semiconductor adj layer). clm. with electrode.clm. with (gan or (gallium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:40
L16	0	(detector or photodetector or photodetecting or detecting).clm. with (semiconductor adj layer). clm. with electrode.clm. with (gan or (gallium adj nitride)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:40
L17	0	(detector or photodetector or photodetecting or detecting).clm. with (semiconductor adj layer). clm. with electrode.clm. and (gan or (gallium adj nitride)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:40
L18	0	((detector or photodetector or photodetecting or detecting).clm. with (semiconductor adj layer). clm. with electrode.clm.) and (gan or (gallium adj nitride)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:41
L19	112	((detector or photodetector or photodetecting or detecting).clm. with (semiconductor adj layer). clm. with electrode.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:41
L20	0	(uv with (detector or photodetector or photodetecting or detecting).clm. with (semiconductor adj layer).clm. with electrode.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:41
L21	0	(uv same (detector or photodetector or photodetecting or detecting).clm. with (semiconductor adj layer).clm. with electrode.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:41
L22	1	(uv same (detector or photodetector or photodetecting or detecting).clm. same (semiconductor adj layer).clm. with electrode.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:41

L23	1	(uv same (detector or photodetector or photodetecting or detecting).clm. same (semiconductor adj layer).clm. same electrode.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:41
L24	1	(uv same (detector or photodetector or photodetecting or detecting).clm. same (semiconductor adj layer) same electrode.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:41
L25	1	(uv same (detector or photodetector or photodetecting or detecting).clm. same (semiconductor adj layer) same electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:41
L26	3	(uv same (detector or photodetector or photodetecting or detecting) same (semiconductor adj layer) same electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:42
L27	107	(uv near photodetector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:42
L28	48	(uv near photodetector) and (Gan or (gallium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:42
L29	1	(uv near photodetector).clm. and (Gan or (gallium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:42
L30	30	(uv near photodetector) and (Gan or (gallium adj nitride)) and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:43
L31	14	(uv near photodetector) and (Gan or (gallium adj nitride)).clm. and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:43
L32	3	(uv near photodetector) and (Gan or (gallium adj nitride)).clm. and electrode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:44

L33	3	(uv near photodetector).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:44
L34	109	(uv near (photodiode or detector or photodetector)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:45
L35	2	(uv near (photodiode or detector or photodetector)).clm. with (gaN or (gallium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:45
L36	4	(uv near (photodiode or detector or photodetector)).clm. and (gaN or (gallium adj nitride)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:46
L37	107	(uv near photodetector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:46
L38	24	(uv near photodetector) and (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:47
L39	5	(uv near photodetector).ti,ab,clm. and (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:48
L40	1	(uv near photodetector).ti,ab,clm. with electrode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:48
L41	2	(uv near photodetector).ti,ab,clm. with electrode.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:48
L42	4	(uv near photodetector) with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:49

L43	25	(uv near photodetector).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:49
L44	8	(uv near photodetector).ti,ab,clm. and (GaN or nitride or (gallium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:49
L45	5	(uv near photodetector).ti,ab,clm. and (GaN or nitride or (gallium adj nitride)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:50
L46	549	((uv near photodetector) or sbd or (barrier adj diode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:50
L47	509	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:51
L48	64	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. with electrode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:51
L49	0	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. with electrode.clm. with (nitride or (gallium adj nitride) or gan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:51
L50	28	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. with electrode.clm. and (nitride or (gallium adj nitride) or gan)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:51
L51	4	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. with electrode.clm. and (nitride or (gallium adj nitride) or gan).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:52
L52	3122	((uv near photodetector) or sbd or (schottky adj barrier adj diode)).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:52

L53	117	((uv near photodetector) or sbd or (schottky adj barrier adj diode)).ti, ab,clm. and (nitride or gan or (gallium adj nitride)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:53
L54	11	((uv near photodetector) or sbd or (schottky adj barrier adj diode)).ti, ab,clm. and (nitride or gan or (gallium adj nitride)).ti,ab,clm. and (semiconductor adj layer).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:53
L55	5	((uv near photodetector) or sbd or (schottky adj barrier adj diode)).ti, ab,clm. and (nitride or gan or (gallium adj nitride)).ti,ab,clm. and (semiconductor adj layer).ti, ab,clm. and electrode.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:53
L56	41	((uv near photodetector) or sbd or (schottky adj barrier adj diode)).ti, ab,clm. and (nitride or gan or (gallium adj nitride)).ti,ab,clm. and electrode.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:54
L57	14	((uv near photodetector) or sbd or (schottky adj barrier adj diode)).ti, ab,clm. and (nitride or gan or (gallium adj nitride)).ti,ab,clm. and electrode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:54
L58	11	((uv near photodetector) or sbd or (schottky adj barrier adj diode)).ti, ab,clm. and (nitride or gan or (gallium adj nitride)).clm. and electrode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:54
L59	8	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. and (nitride or gan or (gallium adj nitride)).clm. and electrode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:55
L60	509	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:55
L61	509	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. and ((uv near photodetector) or sbd or (schottky adj barrier adj diode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:55
L62	62	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. and ((uv near photodetector) or sbd or (schottky adj barrier adj diode)).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:57

L63	4	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. and ((uv near photodetector) or sbd or (schottky adj barrier adj diode)).ti. and (nitride or GaN or (gallium adj nitride)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:56
L64	509	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:57
L65	3	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. with (GaN or nitride or (gallium adj nitride)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:58
L66	3	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. same (GaN or nitride or (gallium adj nitride)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:58
L67	3	((uv near photodetector) or sbd or (schottky adj barrier adj diode)). clm. same (GaN or nitride or (gallium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:58
L68	247	((uv near photodetector) or sbd or (schottky adj barrier adj diode)) same (GaN or nitride or (gallium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:58
L69	102	((uv near photodetector) or sbd or (schottky adj barrier adj diode)) with (GaN or nitride or (gallium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:59
L70	79	((uv near photodetector) or sbd or (schottky adj barrier adj diode)) near10 (GaN or nitride or (gallium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:59
L71	2	((uv near photodetector) or sbd or (schottky adj barrier adj diode)) near10 (GaN or nitride or (gallium adj nitride)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:59
L72	39	((uv near photodetector) or sbd or (schottky adj barrier adj diode)) near10 (GaN or nitride or (gallium adj nitride)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 12:59